

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device includes a semiconductor substrate having ~~one~~ a principal plane on which ~~a plurality of~~ gate, source, and drain electrodes are ~~formed~~ located. A film ~~which is~~ made of a polymer with a low dielectric constant is ~~formed~~ over the gate and drain electrodes ~~so as~~ to insulate the gate and drain electrodes from the source ~~electrode~~ electrodes. A chip surface electrode is ~~formed~~ located over the low-dielectric-constant polymer film and the source electrode, and connected to ~~a~~ ground potential. The source electrode is provided with ~~a~~ the ground potential through the chip surface electrode.